

ABSTRACT OF DISCLOSURE

A semiconductor device wherein the data read time in the case of replacing a defective memory cell with an address storage circuit and a data storage circuit is equal to the data read time in the case of reading data from a memory cell array and chip area is small is provided.

The semiconductor device of the present invention has a plurality of read only storage devices which share an output data line and output data read from a memory cell in response to storage device selection information and address information, and a switching device, which comprises: an address storage circuit for storing the storage device selection information and the address information of the defective memory cell; a data storage circuit for storing the replacement data of the defective memory cell; and a switching circuit which inputs the output data coming via the output data line from the read only storage device and the output data from the data storage circuit and outputs either of these two pieces of output data based on the storage device selection information and the address information stored in the address storage circuit.